

Studies Of Terahertz Radiation From Optically Excited Indium Tin Oxide / Semi Insulating Gallium Arsenide Interface

Anup Kumar Sahoo¹, Chia-Ming Mai¹, Shih-Ying Kang¹, Peichen Yu², and Ci-Ling Pan^{1*}

¹National Tsing Hua University, Hsinchu City, 30013, Taiwan

²National Chiao Tung University, Hsinchu City, 30010, Taiwan

*Corresponding author: Prof. Ci-Ling Pan (e-mail: <u>clpan@phys.nthu.edu.tw</u>)

Objective

Excited the ITO/GaAs samples by using 800 nm wavelength based femtosecond laser source for

Experimental setup



- THz emission
- Compared the power of THz emission from ITO/GaAs interface to bare GaAs substrate,
- Analyzed the effect of THz emission by changing angle of incident excitation and pump power.
- Compared experimental results with optical rectification (OR) theoretical model.
- Dipole radiation model, Fresnel equation, and absorption of ITO were consider for theoretical formulism

Result and discussions





Incident angle (deg.)



Conclusions

References

- We presented our studies on the emission characteristic of ITO/SI-GaAs interface.
- Enhancement is seen in angular dependency experiment with incident angle smaller than 70°, while for power dependency experiment, enhancement is it always found.
- The mechanism further need to investigate by optical rectification theory and photo–Dember effect.

[1] G. Ramakrishnan et al., "Plasmonic-enhanced Terahertz Emission from a Semiconductor/Metal Interface," Appl. Phys. Lett., vol. 104, p. 071104, February. 2014.

[2]. F. Kadlec, P. Kužel, and J.-L. Coutaz, "Optical rectification at metal surfaces," Optics letters, vol. 29, no. 22, pp. 2674-2676, 2004.

[3]. F. Kadlec, P. Kužel, and J.-L. Coutaz, "Study of terahertz radiation generated by optical rectification on thin gold films," Optics letters, vol. 30, no. 11, pp. 1402-1404, 2005

[4Y. Jin, X. Ma, G. Wagoner, M. Alexander, and X. C. Zhang, "Anomalous optically generated THz beams from metal/GaAs interfaces," Applied physics letters, vol. 65, no. 6, pp. 682-684, 1994.